

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2258A

DESCRIPTION

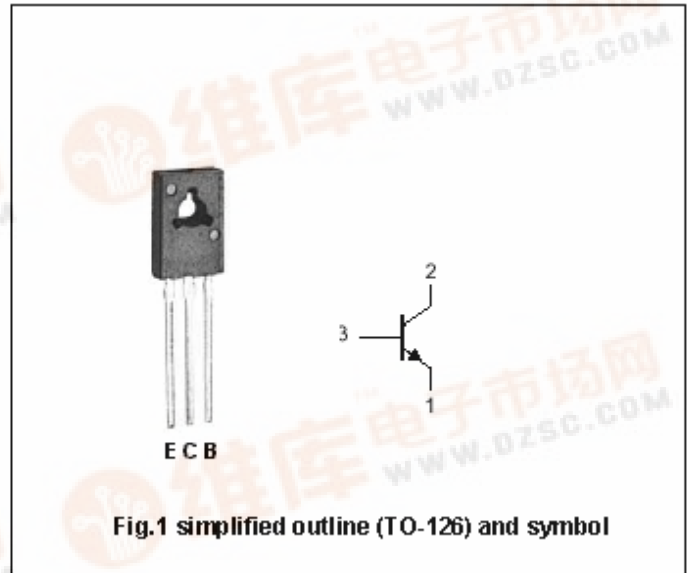
- With TO-126 package
- High transition frequency f_T
- High collector-emitter voltage V_{CEO}

APPLICATIONS

- High voltage general amplifier
- TV video output amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector- emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
I_{CM}	Collector current-peak		0.15	A
P_C	Collector power dissipation	$T_C=25$	1.2^{*1}	W
			4^{*2}	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55 ~ +150	

Note :*1: Without heat sink

*2: With a 100 × 100 × 2 mm A1 heat sink

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CER}	Collector cutoff current	$V_{\text{CE}}=250\text{V}; R_{\text{BE}}=100\text{k}\Omega$			100	μA
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage	$I_{\text{E}}=0.1\text{mA}; I_{\text{C}}=0$	7			V
V_{CESat}	Collector-emitter saturation voltage	$I_{\text{C}}=50\text{mA}; I_{\text{B}}=5\text{mA}$			1.2	V
V_{BE}	Base-emitter voltage	$I_{\text{C}}=40\text{mA}; V_{\text{CE}}=20\text{V}$			1.2	V
$h_{\text{FE-1}}$	DC current gain	$I_{\text{C}}=40\text{mA}; V_{\text{CE}}=20\text{V}$	40			
$h_{\text{FE-2}}$	DC current gain	$I_{\text{C}}=5\text{mA}; V_{\text{CE}}=50\text{V}$	30			
C_{OB}	Output capacitance	$I_{\text{E}}=0; V_{\text{CB}}=50\text{V}; f=1\text{MHz}$		3	4.5	pF
f_{T}	Transition frequency	$I_{\text{E}}=-10\text{mA}; V_{\text{CE}}=10\text{V}$		100		MHz

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PACKAGE OUTLINE

